

植入步驟	相關之電性項目	針對每個項目作說明
Poly-Si gate		
V_T adjustment		
LDD		
halo		
APT		
well		

10. 以下四個，有哪幾個可明顯反應出 halo implant 過淡？請說明理由(a)lower junction breakdown voltage(b)lower gate oxide breakdown voltage(c)lower well resistance(d)lower punch through voltage
11. 以下四個，有哪幾個可明顯反應出 APT implant 過淡？請說明理由(a)higher junction breakdown voltage(b)lower junction breakdown voltage(c)higher well resistance(d)lower well resistance